TRANSISTORS, POWER, NPN,

BASED ON TYPE 2N6307

ESCC Detail Specification No. 5208/007

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Pages 1 to 24

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space components
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DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
'A'	Feb. '92	This Issue incorporates all modifications agreed on the basis of Policy DCR 21016 for adaptation to new qualification requirements		
		P1.	Cover page	None
		P2.	DCN	None
		P4.	Table of Contents : "Appendices" Title added	21019
		P5.	Para. 1.2 : Paragraph amended	21021
		P6.	Table 1(a) : "Lead Material and/or Finish" column amended	21025
		P11.	Para. 2 : MIL-STD-1276 deleted, "ESA/SCC Basic Spec. No. 23500" added	21025
			Para. 4.1 : Additional text added	21019
			Para. 4.2.2 : PIND deviation deleted	21043
		P12.	Para. 4.2.3 : H.T.R.B. deviation deleted	23499
		P13.	Para. 4.4.2 : Paragraph amended	21025
		P18.	Table 3 : Reference to Note 2 deleted, Note 1 put under this table	21047
		This document has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.		
'B'	Aug. '96	P1.	Cover page	None
		P2.	DCN	None
		P5.	Para. 1.7 : Text amended	21083

TABLE OF CONTENTS

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Transistor, Power, NPN, based on Type 2N6307.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

See Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the transistors specified herein, are scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The applicable derating information for the transistors specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the transistors specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification of the transistors specified herein, is shown in Figure 3.

1.7 HIGH TEMPERATURE TEST PRECAUTIONS

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in a 100% inert atmosphere.

TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND FINISH
01	TO3	2	D2
02	TO3	2	D3 or D4

TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Collector-Base Voltage	V_{CB}	600	Vdc	
2	Collector-Emitter Voltage	V_{CE}	300	Vdc	
3	Emitter-Base Voltage	V_{EB}	8.0	Vdc	
4	Continuous Collector Current	I_C	8.0	Adc	
5	Continuous Base Current	I_B	4.0	Adc	
6	Continuous Power Dissipation	P_{tot}	175 100	W	Note 1 Note 2
7	Operating Temperature Range	T_{op}	−65 to +200	°C	
8	Storage Temperature Range	T_{stg}	−65 to +200	°C	
9	Soldering Temperature	T_{sol}	+260	°C	Note 3

NOTES

1. At T_{case} = +25°C.
2. At T_{case} = +100°C. For derating, see Figure 1.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the can and the same lead shall not be resoldered until 3 minutes have elapsed.

FIGURE 1 - DEVICE DISSIPATION DERATING WITH TEMPERATURE

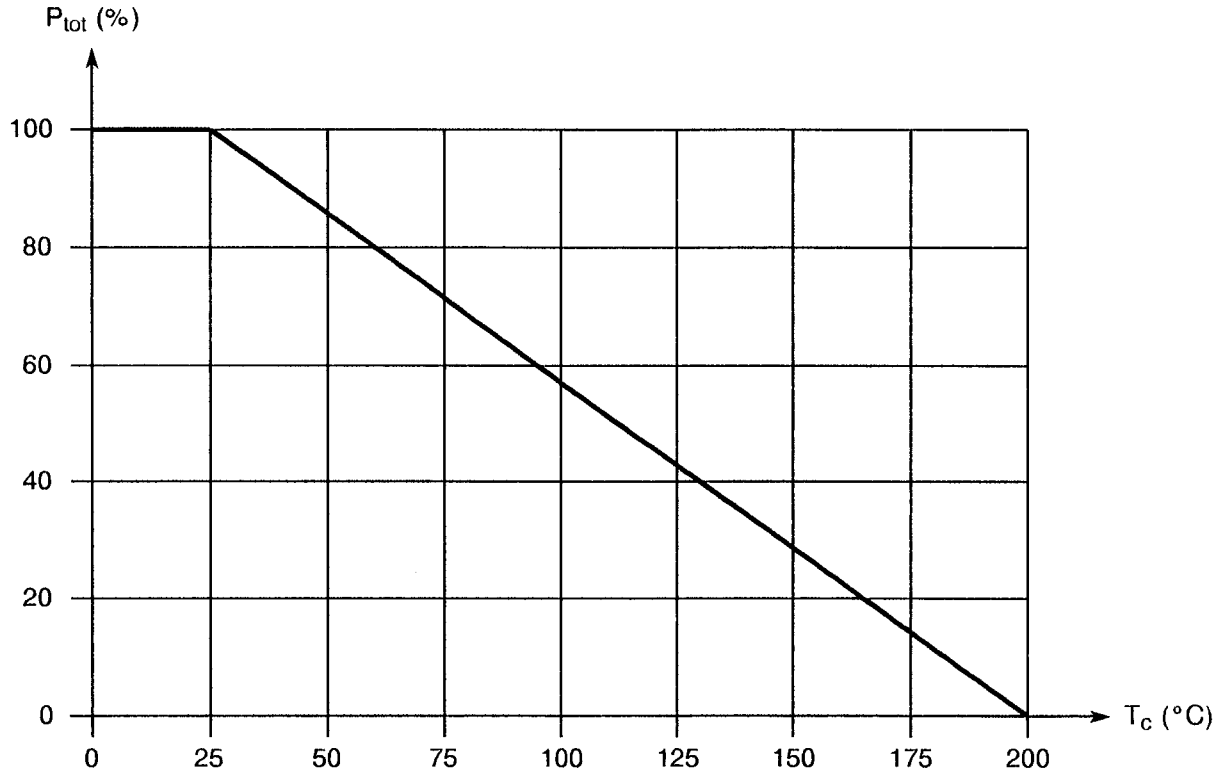
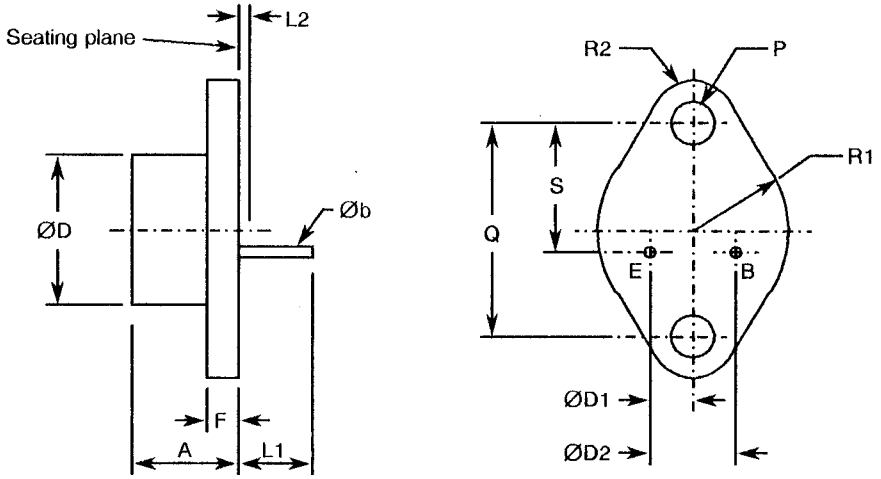


FIGURE 2 - PHYSICAL DIMENSIONS

TO3 CASE



SYMBOL	INCHES		MILLIMETRES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.250	0.450	6.35	11.43	
Øb	0.038	0.043	0.97	1.09	1, 2
ØD	-	0.875	-	22.23	
ØD1	0.205	0.225	5.21	5.72	
ØD2	0.420	0.440	10.67	11.18	
F	0.060	0.135	1.52	3.43	
L1	0.312	0.500	7.92	12.70	
L2	-	0.050	-	1.27	3
P	0.151	0.161	3.84	4.09	
Q	1.177	1.197	29.90	30.40	
R1	0.495	0.525	12.57	13.34	
R2	0.131	0.188	3.33	4.78	
S	0.655	0.675	16.64	17.15	

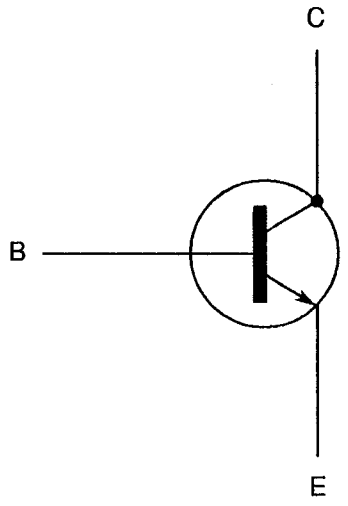
NOTES: See Page 10.

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES

1. Both leads.
2. Øb applies between L1 and L2.
3. The diameter of leads within this zone is not controlled.

FIGURE 3 - FUNCTIONAL DIAGRAM



B = Base.
E = Emitter.
C = Collector.

NOTES

1. The collector is electrically connected to the case.

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

(a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.

(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

(c) ESA/SCC Basic Specification No. 23500, Requirements for Lead Materials and Finishes for Components for Space Application.

(d) MIL-STD-105, Sampling Procedure and Tables for Inspection by Attributes.

(e) MIL-STD-883, Test Methods and Procedures for Microelectronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviation shall be used:-

$E_{S/B}$ = Second Breakdown Energy.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the transistors specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II)

Add the following test, after Para. 9.2.1, "Bond Strength Test":-

Die Shear Test in accordance with MIL-STD-883, Method 2019, to be performed on 3 devices with no failures permitted.

Para. 9.6, "Constant Acceleration": Change Acceleration Level to 10000g.

4.2.3 Deviations from Burn-in Tests (Chart III)

None.

4.2.4 Deviations from Qualification Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the transistors specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the transistors specified herein shall be 22.5 grammes.

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition: 'A', Tension.
Applied Force: 10 lb. force.
Duration: 15 seconds.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the transistors specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals, and the lid shall be welded, brazed or preform soldered.

4.4.2 Lead Material and Finish

The lead material shall be Type 'D' with either Type '2' or Type '3 or 4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

(a) Lead Identification.

(b) The SCC Component Number.

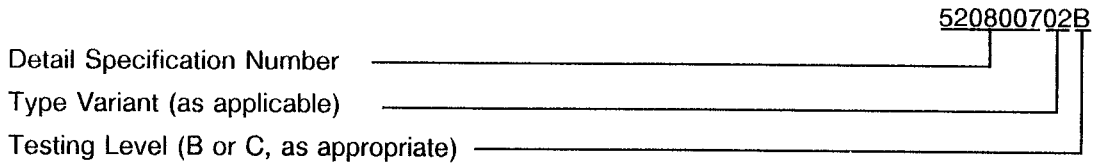
(c) Traceability Information.

4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

(a) Lead Identification.

(b) The SCC Component Number.

(c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +25 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at $T_{amb} = +150(+0-5)$ °C and $-55(+5-0)$ °C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 are shown, where applicable, in MIL-STD-750 and in Figure 4 of this specification.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +25 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Burn-in

Not applicable.

4.7.4 Conditions for High Temperature Reverse Bias

The requirements for high temperature reverse bias are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for high temperature reverse bias shall be as specified in Table 5 of this specification.

4.7.5 Electrical Circuits for High Temperature Reverse Bias

Not applicable.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST FIG.	TEST CONDITIONS	LIMITS		UNIT
						MIN.	MAX.	
1	Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	3011 Bias Cond. D	-	I_C = 100mAdc I_B = 0Adc Note 1	300	-	V
2	Base Saturation Voltage	$V_{BE(SAT)}$	3066 Bias Cond. A	-	I_C = 3.0Adc I_B = 0.6Adc	-	1.8	V
3	Collector Saturation Voltage	$V_{CE(SAT)1}$	3071	-	I_C = 3.0Adc I_B = 0.6Adc	-	1.0	V
4	Collector Saturation Voltage	$V_{CE(SAT)2}$	3071	-	I_C = 8.0Adc I_B = 2.0Adc	-	5.0	V
5	Emitter-Base Reverse Current	I_{EBO}	3061 Bias Cond. D	-	V_{EB} = 8.0Vdc I_C = 0Adc	-	1.0	V
6	Collector Cut-off Current	I_{CEX}	3041 Bias Cond. A	-	V_{CE} = 600Vdc V_{EB} = − 1.5Vdc	-	500	µA
7	D.C. Forward Current Transistor Ratio	h_{FE1}	3076	-	V_{CE} = 5.0Vdc I_C = 3.0Adc Note 1	15	75	-
8	D.C. Forward Current Transfer Ratio	h_{FE2}	3076	-	V_{CE} = 5.0Vdc I_C = 6.0Adc Note 1	8.0	-	-

NOTES: See Page 17.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST FIG.	TEST CONDITIONS	LIMITS		UNIT
						MIN.	MAX.	
9	Second Breakdown Energy	$E_{S/B}$	-	4(a)	I_C = 3.0Adc L = 40mH	180	-	mJ
10	High Frequency Forward Current Gain	h_{fe}	3306	-	V_{CE} = 10Vdc I_C = 0.3Adc f = 1.0MHz Note 1	5.0	-	-
11	Output Capacitance	C_{obo}	3236	-	V_{CB} = 10Vdc I_E = 0Adc f = 0.1MHz Note 2	-	250	pF
12	Pulse Rise Time	t_r	-	4(b)	V_{CC} = 125Vdc I_C = 3.0Adc I_B = 0.6Adc Note 2	-	0.6	µs
13	Pulse Storage Time	t_s	-	4(b)	V_{CC} = 125Vdc I_C = 3.0Adc I_{B1} = 0.6Adc I_{B2} = 1.5Adc Note 2	-	1.6	µs
14	Pulse Fall Time	t_f	-	4(b)	V_{CC} = 125Vdc I_C = 3.0Adc I_{B1} = 0.6Adc I_{B2} = 1.5Adc Note 2	-	0.4	µs

NOTES

1. Pulse measurement: Pulse Length ≤ 300µs, Duty Cycle ≤ 2.0%.
2. If more than 20 units have to be measured, the measurements shall be made on a sample basis in accordance with Level II, Table IIa, AQL = 1.0 of MIL-STD-105.

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

TABLE 3(a) - T_{amb} = +150(+0−5)°C

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST FIG.	TEST CONDITIONS	LIMITS		UNIT
						MIN.	MAX.	
6	Collector Cut-off Current	I_{CEX}	3041 Bias Cond. A	-	V_{CE} = 600Vdc V_{BE} = −1.5Vdc	-	2.5	mA

TABLE 3(b) - T_{amb} = −55(+5−0)°C

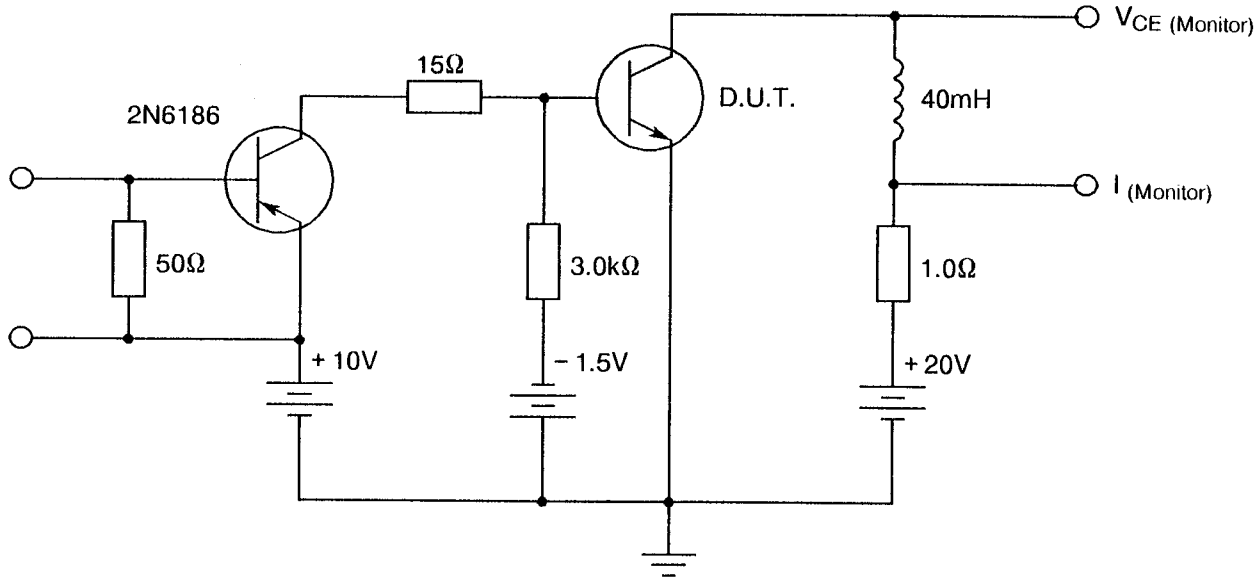
No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST FIG.	TEST CONDITIONS	LIMITS		UNIT
						MIN.	MAX.	
7	D.C. Forward Current Transfer Ratio	h_{FE1}	3076	-	V_{CE} = 5.0Vdc I_C = 3.0Adc Note 1	9.0	-	-

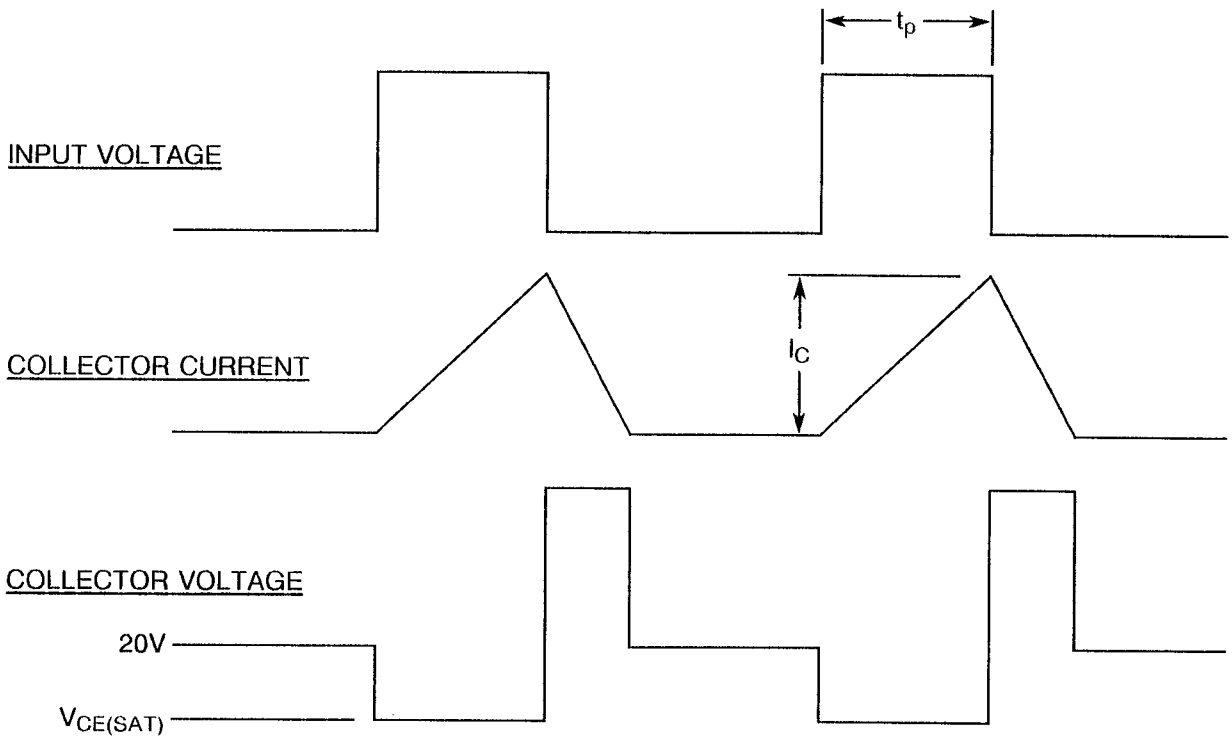
NOTES

1. Pulsed measurement: Pulse Length ≤300µs, Duty Cycle ≤2.0%.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - SECOND BREAKDOWN ENERGY



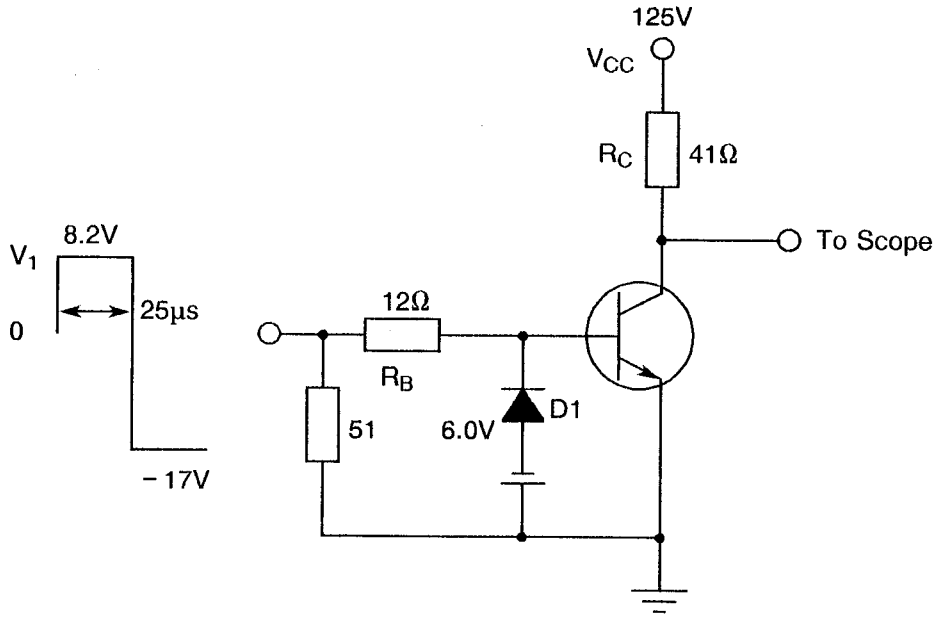


NOTES

1. Impulse width t_p is to adjust for a collector current of 3.0Adc.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(b) - SWITCHING TIMES



NOTES

1. Input pulse: Duty Cycle = 1.0%, $t_r = t_f < 10$ns.
2. D1: 1N3679 or equivalent.

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
6	Collector Cut-off Current	I_{CEX}	As per Table 2	As per Table 2	± 80	µA
7	D.C. Forward Current Transfer Ratio	h_{FE1}	As per Table 2	As per Table 2	± 25	%
3	Collector Saturation Voltage	$V_{CE(SAT)1}$	As per Table 2	As per Table 2	± 60	mV

TABLE 5(a) - CONDITIONS FOR BURN-IN AND OPERATING LIFE TESTS

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Case Temperature	T_C	+ 100(+ 0 − 5)	°C
2	Power Dissipation	P_{tot}	100	W
3	Collector-Base Voltage	V_{CB}	20	V
4	Test Method 1039 of MIL-STD-750	-	B	-

TABLE 5(b) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T_{amb}	+ 150(+ 0 − 5)	°C
2	Reverse Bias	V_{CB}	− 480	V
3	Test Method 1039 of MIL-STD-750	-	A	-
4	Duration	-	48 ± 4	Hrs

4.8 ENVIRONMENTAL AND ENDURANCE TESTS

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at $T_{amb} = +25 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are scheduled in Table 6.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance tests are scheduled in Table 6. The measurements shall be performed at $T_{amb} = +25 \pm 3$ °C.

4.8.4 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 Electrical Circuits for Operating Life Tests

Not applicable.

4.8.6 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The conditions for high temperature storage shall be $T_{amb} = +200(+0-5)$°C.

TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
6	Collector Cut-off Current	I_{CEX}	As per Table 2	As per Table 2	-	500	µA
7	D.C. Forward Current Transfer Ratio	h_{FE1}	As per Table 2	As per Table 2	15	75	-
3	Collector-Emitter Saturation Voltage	$V_{CE(SAT)1}$	As per Table 2	As per Table 2	-	1.0	V